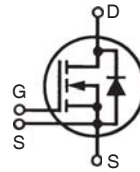


Linear Power MOSFET With Extended FBSOA

IXTN17N120L

N-Channel Enhancement Mode
Avalanche Rated

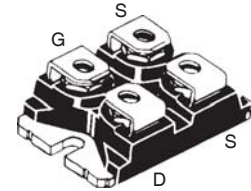


$$V_{DSS} = 1200V$$

$$I_{D25} = 17A$$

$$R_{DS(on)} \leq 990m\Omega$$

miniBLOC, SOT-227 B (IXTN)
E153432



G = Gate D = Drain
S = Source

Either Source terminal S can be used as the Source terminal or Kelvin Source (gate return) terminal.

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1200	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	17	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	30	A
P_D	$T_C = 25^\circ C$	700	W
T_J		-55 to +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 to +150	$^\circ C$
V_{ISOL}	50/60 Hz, RMS, $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1mA$, $t = 1s$	3000	V~
M_d	Mounting torque for Base Plate	1.5/13	Nm/lb.in.
	Terminal connection torque	1.3/11.5	Nm/lb.in.
Weight		30	g

Features

- Designed for linear operation
- International standard package
- Molding epoxy meets UL94 V-0 flammability classification
- miniBLOC with Aluminum nitride isolation

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Programmable loads
- Current regulators
- DC-DC converters
- Battery chargers
- DC choppers
- Temperature and lighting controls

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	1200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$			50 μA
	$V_{GS} = 0V$ $T_J = 125^\circ C$			2 mA
$R_{DS(on)}$	$V_{GS} = 20V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			990 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	3.5	5.3	7.5 S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		8300	pF
C_{oss}			525	pF
C_{rss}			90	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		40	ns
t_{ri}			30	ns
$t_{d(off)}$			110	ns
t_{fi}			83	ns
$Q_{g(on)}$		$V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		155
Q_{gs}			40	nC
Q_{gd}			60	nC
R_{thJC}				0.18 $^\circ\text{C/W}$
R_{thCS}		0.05		$^\circ\text{C/W}$

Safe Operating Area Specification

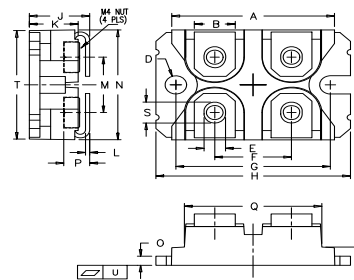
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 800\text{V}$, $I_D = 300\text{mA}$, $T_C = 90^\circ\text{C}$	240		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			17 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			30 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.3 V
t_{rr}	$I_F = I_S$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$		1830	ns

Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

SOT-227B (IXTN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

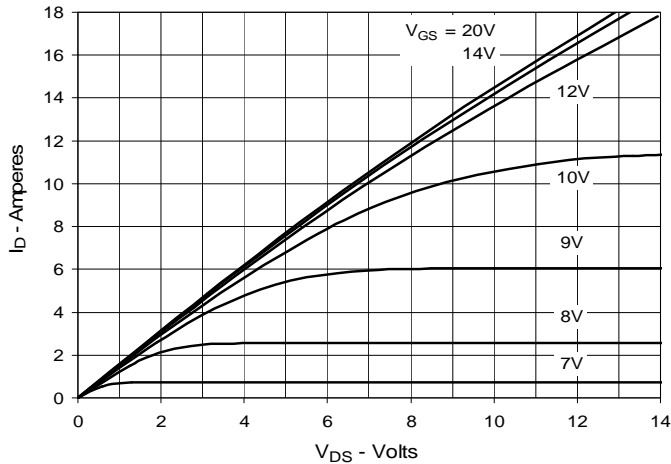


Fig. 2. Extended Output Characteristics @ 25°C

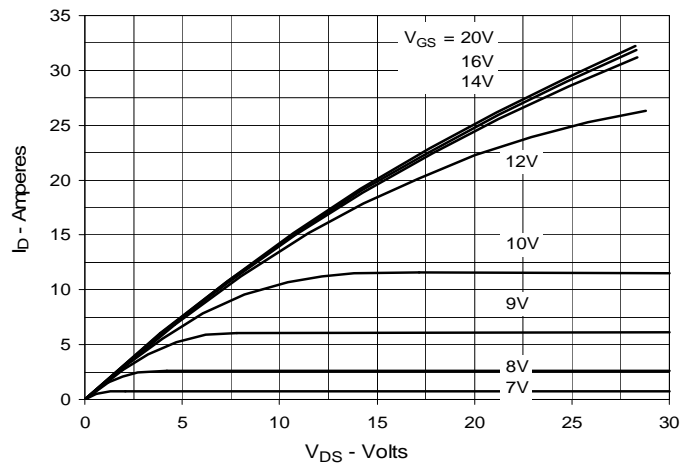


Fig. 3. Output Characteristics @ 125°C

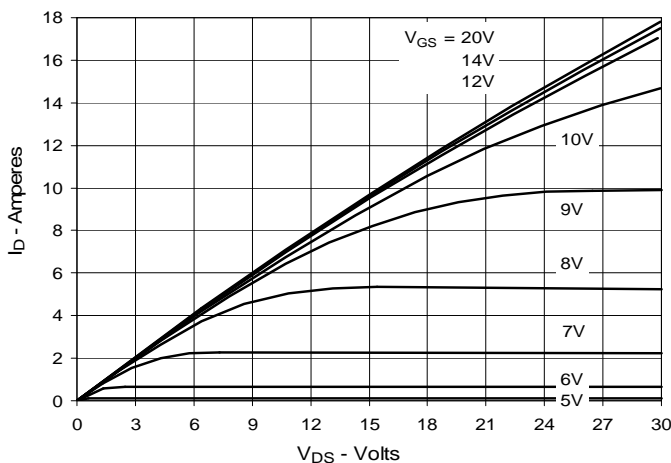


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 8.5A$ Value vs. Junction Temperature

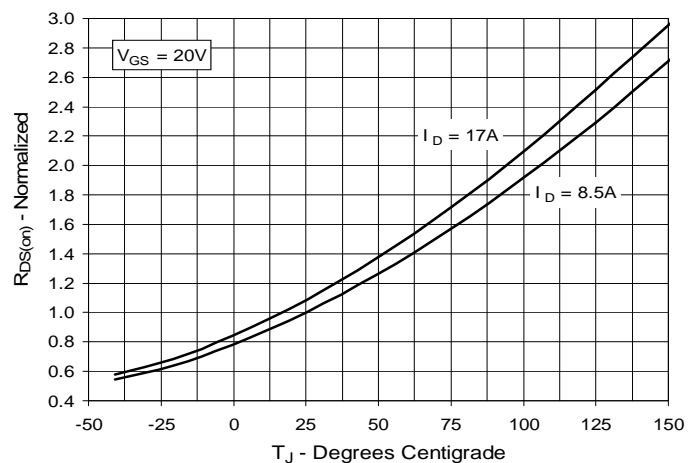


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 8.5A$ Value vs. Drain Current

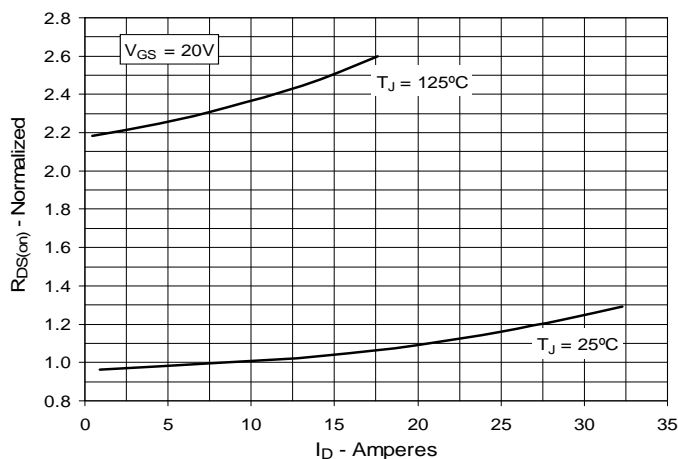


Fig. 6. Maximum Drain Current vs. Case Temperature

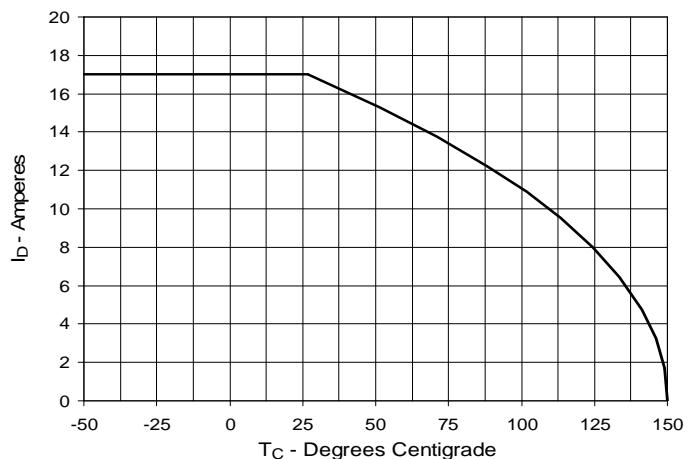


Fig. 7. Input Admittance

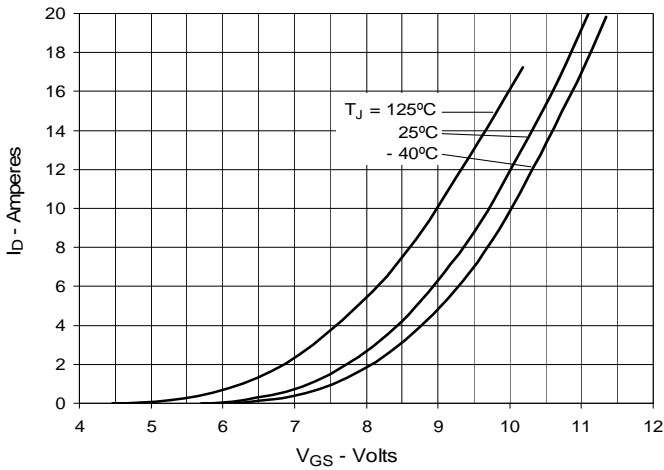


Fig. 8. Transconductance

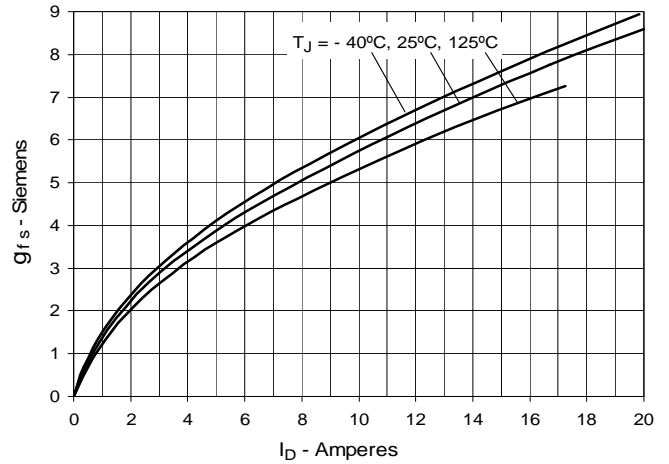


Fig. 9. Forward Voltage Drop of Intrinsic Diode

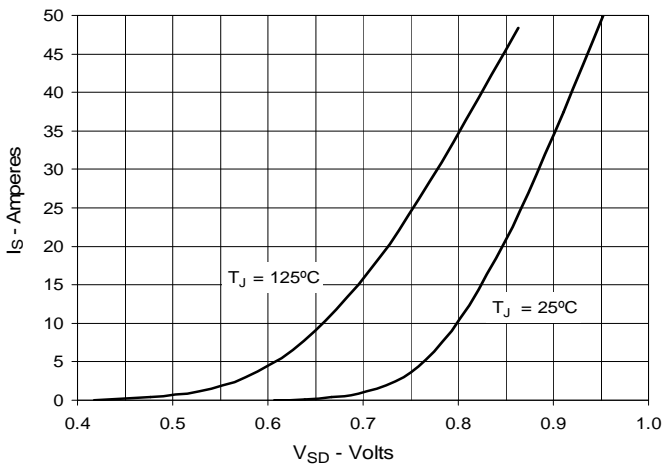


Fig. 10. Gate Charge

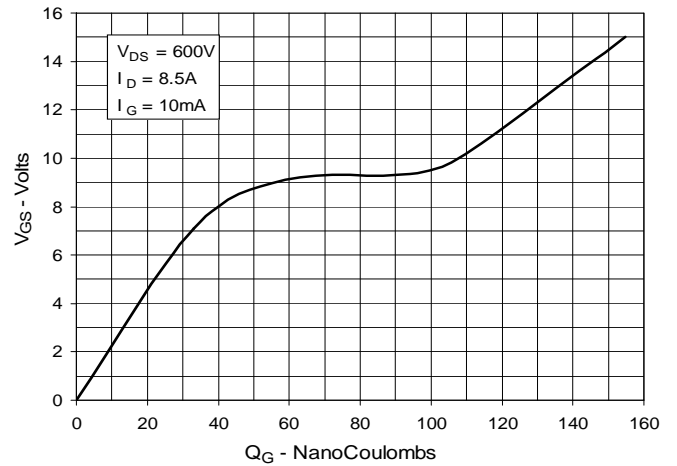


Fig. 11. Capacitance

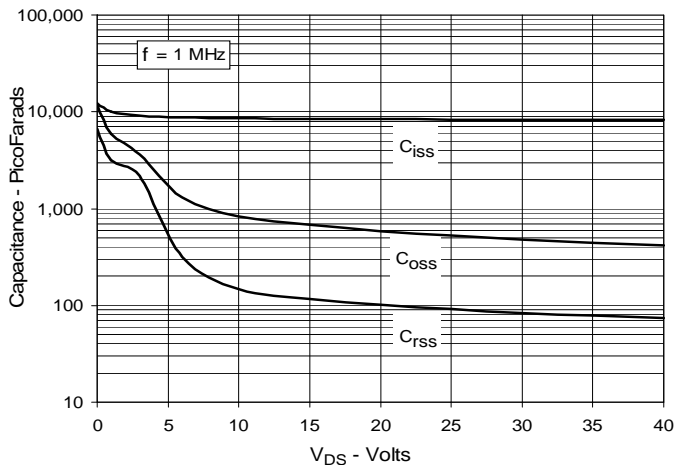


Fig. 12. Maximum Transient Thermal Impedance

